

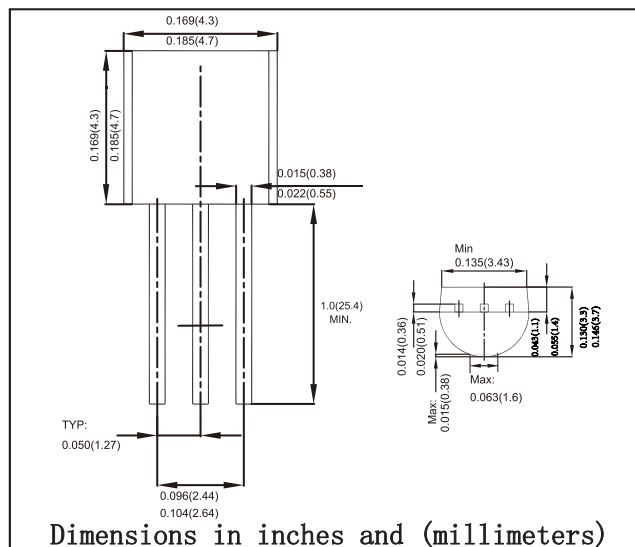
TO-92 Plastic-Encapsulate Transistors

FEATURES

- NPN Transistors
- Low switching loss and high reliability
- High temperature characteristics
- Reverse leakage

MECHANICAL DATA

- Case style:TO-92 molded plastic
- Mounting position:any



MAXIMUM RATINGS

(Ta=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector Base Voltage	600	V
V _{CEO}	Collector Emitter Voltage	400	V
V _{EBO}	Emitter Base Voltage	9	V
I _C	Collector Current	1	A
P _{tot}	Total Power Dissipation	1.25	mW
T _j	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55 ~ +150	°C

Electrical Characteristics (T_a=25°C unless otherwise specified)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
V _{(BR)CBO}	Collector-base breakdown voltage	I _C = 0.1mA, I _E = 0	600			V
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C = 1mA, I _B = 0	400			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E = 0.1mA, I _C = 0	9			V
I _{CBO}	Collector cut-off current	V _{CB} = 600V, I _E = 0			10	μA
I _{EBO}	Emitter cut-off current	V _{EB} = 9V, I _C = 0			10	μA
h _{FE}	DC current gain	V _{CE} = 5V, I _C = 200mA	15		30	
V _{CE(sat)}	Collector-emitter saturation voltage	I _C = 500mA, I _B = 100mA			0.5	V
V _{ECF}		I _C = 1.5A			2.5	V
t _s	Storage time	UI9600A, I _C = 0.25A	1.5		4.0	μs
f _T	Transition frequency	V _{CE} = 10V, I _C = 0.1A, f = 1MHZ	5			MHz

RATINGS AND CHARACTERISTIC CURVES

Typical Characteristics

